

Performance

- Technology: 0.35um Power GaN HEMT
- Frequency: 2.2~2.4GHz
- Typical Pout : 58dBm
- Typical Gain: 12dB
- Typical PAE: 60%
- Bias: 48V/-3V
- Package: Metal Ceramic

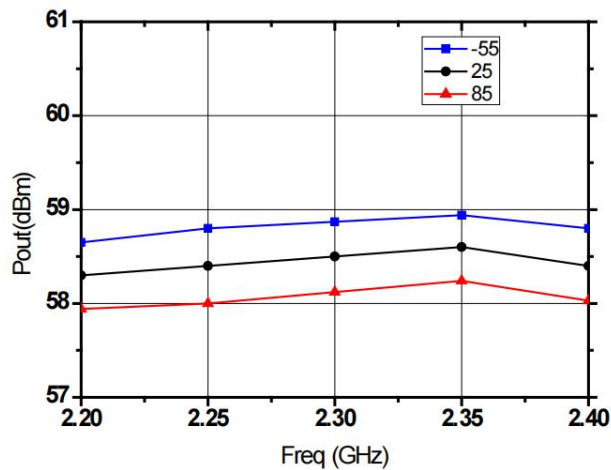


Electrical Specifications ($T_A=25^{\circ}\text{C}$, $V_d=48\text{V}$, $P_L=1\text{us}$, $D.C=1\%$, $V_g=-3\text{V}$, $F: 2.2-2.4\text{GHz}$)

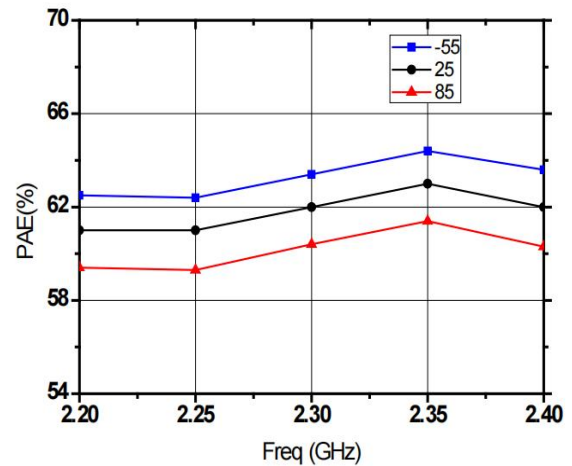
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	58	-	dBm
Gp	Power Gain	-	12	-	dB
η_{add}	Power Added Efficiency	-	60	-	%
Rth	Thermal Resistance	-	-	0.15	$^{\circ}\text{C/W}$

Test Curves

Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.

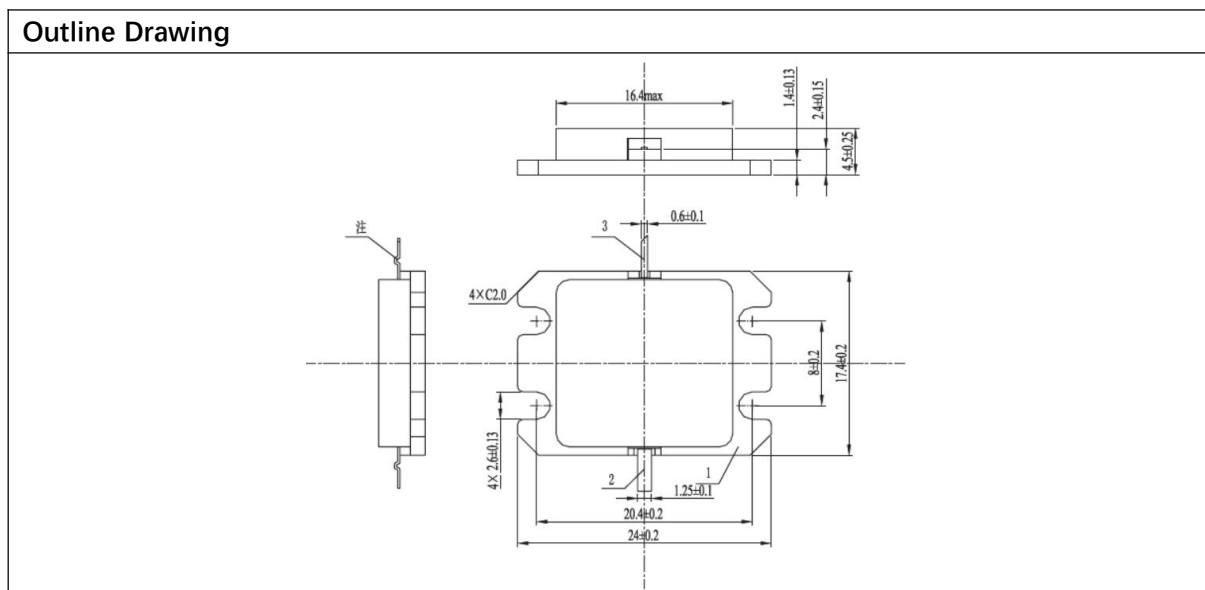


Absolute Max Ratings (TA=25°C)

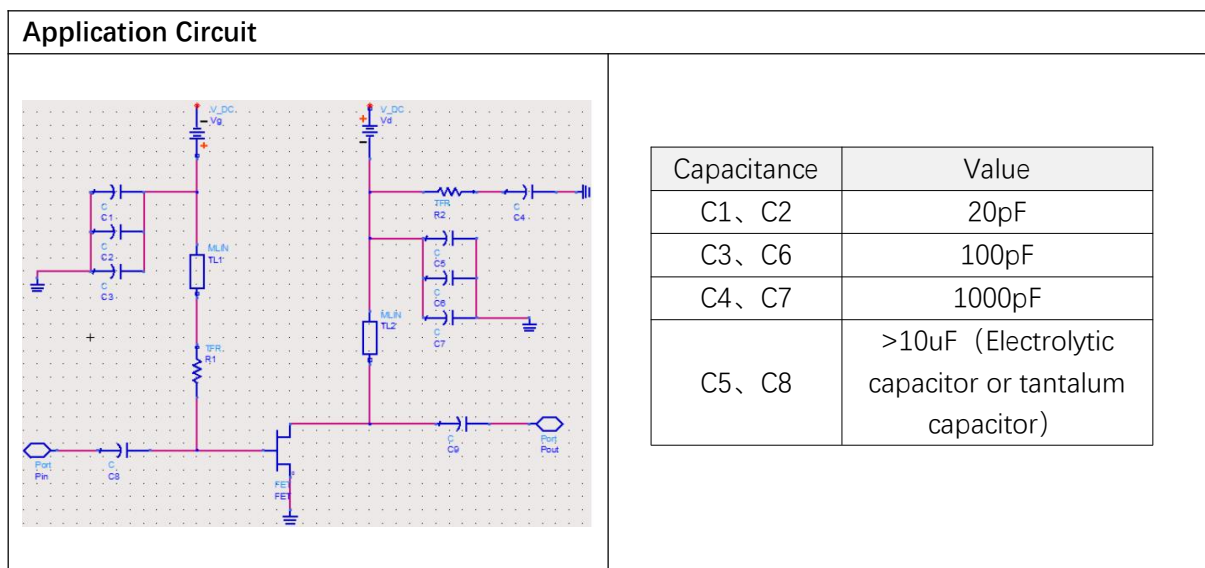
Symbol	Parameter	Value	Remark
Vd	Drain Voltage	60V	
Vg	Grid Voltage	-5V	
Tch	Channel Temperature	225°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~175°C	
Tc	Operating Temperature	-55~85°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing



Application Circuit



Note:

- (1) This product is an internal matching tube, with input and output impedance values of 50 ohms;
- (2) The power-on sequence shall be in strict accordance with the sequence of applying negative power first and then positive power. When power-off, the leakage voltage shall be reduced first and then the grid voltage shall be reduced;
- (3) This product is a high-power device. Pay attention to heat dissipation during use. The higher the shell temperature is, the shorter the service life is. The service temperature should not be higher than 80 °C;
- (4) This product is an electrostatic sensitive device. It needs to pay attention to electrostatic protection during storage and use, and it needs to be grounded well during use.